



Modeling of Short-Channel GaN HEMTs for Ultra-high Frequency Applications



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Current status/stage of your JDP: Comprehensive exam passed,
Course work – 6 credits at NYCU and 7 credits in IIT Delhi, 7 semesters
completed in Jan 2024 (including 1 sem in NYCU).

- Reliability assessment of SCE GaN HEMT by TCAD simulation
- Accurate determination of energy states by current-transient measurement at different ambient temperatures.
- Development of comprehensive model calibration procedure (DC/ RF) for TCAD simulation
- Conference paper Published:
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